	#### _ T	Search Text	DB	Time stamp
L Number	Hits 2	("6147852").PN.	USPAT;	2004/04/10 20:41
1	2	(0147032 7.11	US-PGPUB; EPO; JPO; DERWENT;	
2	2	("6075271").PN.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/10 21:32
3	2292	((257/168) or (257/173) or (257/355) or (257/358) or (257/360) or (257/361) or (257/362) or (257/363) or (257/370) or (257/373)).CCLS.	IBM_TDB USPAT; US-PGPUB	2004/04/10 21:35
4	257	(((257/168) or (257/173) or (257/355) or (257/358) or (257/360) or (257/361) or (257/362) or (257/363) or (257/370) or (257/373)).CCLS.) and (electrostatic adj discharge esd) near3 (protection protecting) and (resistances resistance resistor resistors) near4 (series breakdown break-down common)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/10 22:07
5	1166		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/10 22:07
6	909	((electrostatic adj discharge esd) near3 (protection protecting) and (resistances resistance resistor resistors) near4 (series breakdown break-down common)) not ((((257/168) or (257/173) or (257/355) or (257/358) or (257/360) or (257/361) or (257/362) or (257/363) or (257/370) or (257/373)).CCLS.) and (electrostatic adj discharge esd) near3 (protection protecting) and (resistances resistance resistor resistors) near4 (series	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/10 22:09
7	17	breakdown break-down common) ((electrostatic adj discharge esd) near3 (protection protecting) and (resistances resistance resistor resistors) near4 (series breakdown break-down common)) not ((((257/168) or (257/173) or (257/355) or (257/358) or (257/360) or (257/361) or (257/362) or (257/363) or (257/370) or (257/373)).CCLS.) and (electrostatic adj discharge esd) near3 (protection protecting) and (resistances resistance resistor resistors) near4 (series	EPO; JPO; IBM_TDB	2004/04/10 22:09
-	92	breakdown break-down common)) (257/168).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/10 18:36
-	312	(257/173).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05 20:15
_	9	(("257/168").CCLS.) and (("257/173").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/02/05 20:15
_	4	plurality adj2 bipolar adj transistor.clm. and esd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/05 20:16

				2002/02/05 20-17
-	36	((("257/168").CCLS.) or	USPAT; US-PGPUB;	2002/02/05 20:17
		(("257/173").CCLS.)) and esd and bipolar adj transistor	EPO; JPO;	
		adj Clansistoi	DERWENT;	
			IBM_TDB	
-	40	(plurality adj2 bipolar adj	USPAT;	2002/02/05 20:22
		transistor.clm. and esd) or	US-PGPUB; EPO; JPO;	
		(((("257/168").CCLS.) or (("257/173").CCLS.)) and esd and bipolar	DERWENT;	
		adj transistor)	IBM TDB	
	547	resistor and esd and bipolar adj	USPĀT;	2002/02/05 20:23
		transistor	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
	117	resistor and esd and ((parallel or	USPAT;	2002/02/05 20:34
_	11/	lateral\$2) near3 bipolar adj transistor)	US-PGPUB;	
		1400241,0, 1411	EPO; JPO;	
			DERWENT;	İ
			IBM_TDB EPO	2002/02/05 20:35
-	152 395	charpentier.in. (("257/168").CCLS.) or (("257/173").CCLS.)	USPAT;	2003/06/07 17:37
_	395	((257/100).0015.) 01 ((257/175).0016.)	US-PGPUB;	
	1		EPO; JPO;	
		·	DERWENT;	
		(48057/1728)	IBM_TDB	2002/02/06 08:43
_	166	(("257/168").CCLS.) or (("257/173").CCLS.)	USPAT; US-PGPUB;	2002/02/00 00.43
		<pre>and ((esd or electrostatic adj discharge) near12 protect\$3)</pre>	EPO; JPO;	
		near12 proceed(43)	DERWENT;	
			IBM_TDB	
_	97		USPAT;	2002/02/06 08:47
		and ((esd or electrostatic adj discharge)	US-PGPUB; EPO; JPO;	
		near12 protect\$3) and (resist\$3 near15 bipolar adj transistor)	DERWENT;	
		biporar adj cransiscor,	IBM TDB	
_	94	(("257/168").CCLS.) or (("257/173").CCLS.)	USPAT;	2002/02/06 08:48
		and ((esd or electrostatic adj discharge)	US-PGPUB;	
		near12 protect\$3) and (resist\$3 near15	EPO; JPO; DERWENT;	
		bipolar adj transistor) and (plurality near12 transistor)	IBM TDB	
_	94	(("257/168").CCLS.) or (("257/173").CCLS.)	USPAT;	2002/02/06 08:51
		and ((esd or electrostatic adj discharge)	US-PGPUB;	
		near12 protect\$3) and (resist\$3 near15	EPO; JPO;	
		bipolar adj transistor) and (plurality	DERWENT; IBM TDB	
		near12 transistor) and (parallel near12 (transistor or connect\$3 or load))	TDM_TDD	
_	93	1 '	USPAT;	2002/02/06 08:51
		and ((esd or electrostatic adj discharge)	US-PGPUB;	
		near12 protect\$3) and (resist\$3 near15	EPO; JPO;	
		bipolar adj transistor) and (plurality	DERWENT; IBM TDB	
		near12 transistor) and (parallel near12 (transistor or connect\$3 or load)) and	100_100	
		bipolar.ti,ab.		
<u>=</u>	93	(("257/168").CCLS.) or (("257/173").CCLS.)	USPAT;	2002/02/06 08:52
		and ((esd or electrostatic adj discharge)	US-PGPUB;	
		near12 protect\$3) and (resist\$3 near15	EPO; JPO; DERWENT;	
		bipolar adj transistor) and (plurality near12 transistor) and (parallel near12	IBM TDB	
		(transistor or connect\$3 or load)) and		
		bipolar.ti, ab. and (ic or integrated adj		
		circuit)	HODE	2002/02/06 00:54
-	93		USPAT; US-PGPUB;	2002/02/06 08:54
	•	<pre>and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15</pre>	EPO; JPO;	
		bipolar adj transistor) and (plurality	DERWENT;	
		near12 transistor) and (parallel near12	IBM_TDB	
		(transistor or connect\$3 or load)) and		
		bipolar.ti, ab. and (ic or integrated adj		
	1	circuit) and bus		<u> </u>

_	93	(("257/168").CCLS.) or (("257/173").CCLS.) and ((esd or electrostatic adj discharge) near12 protect\$3) and (resist\$3 near15 bipolar adj transistor) and (plurality near12 transistor) and (parallel near12 (transistor or connect\$3 or load)) and bipolar.ti,ab. and (ic or integrated adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 08:54
_	31	circuit) and bus	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 08:57
_	20	(((("257/168").CCLS.) or (("257/173").CCLS.)) and esd adj protect\$3.ti,ab.) and bipolar adj2 transistor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 08:57
_	16	((((("257/168").CCLS.) or (("257/173").CCLS.)) and esd adj protect\$3.ti,ab.) and bipolar adj2 transistor) and resist\$3	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 09:14
	3	5043782.pn.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 09:16
_	2	5708550.pn.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/02/06 09:15
	2	jp-61292351\$-\$.did.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/02/06 09:16
_	395	((257/168) or (257/173)).CCLS.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/02/06 11:37
	0	("L3 and esd adj2 protection.ti,ab.").PN.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 10:58
_	29	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/02/06 10:58
_	7	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar.ti,ab.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/02/06 10:59
_	0	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar.ti,ab. and plurality adj2 bipolar	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/02/06 10:59
-	0	((("257/168") or ("257/173")).CCLS.) and esd adj2 protection.ti,ab. and bipolar.ti,ab. and plurality adj2 transistor	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/02/06 11:00

_	15		USPAT;	2002/02/06 11:	00
		esd adj2 protection.ti,ab. and bipolar adj	US-PGPUB;		
		transistor	EPO; JPO;		
			DERWENT; IBM TDB		
	12	((("257/168") or ("257/173")).CCLS.) and	USPAT;	2002/02/06 11:	02
_	12	esd adj2 protection.ti,ab. and bipolar adj	US-PGPUB;	2002/02/00 11.	02
	8	transistor and resist\$3	EPO; JPO;		
		Clansistor and lesistys	DERWENT;		
			IBM TDB		
_	5	((("257/168") or ("257/173")).CCLS.) and	USPAT;	2002/02/06 11:	02
		esd adj2 protection.ti,ab. and bipolar adj	US-PGPUB;		
1		transistor and resist\$3 and parallel	EPO; JPO;		
			DERWENT;		
			IBM_TDB		
-	3		USPAT;	2002/02/06 11:	48
		esd adj protection.ti,ab. and bipolar adj	US-PGPUB;		
		transistor.ti,ab.	EPO; JPO;		
			DERWENT;		
	101	and add mentantion to the and himalar add	IBM_TDB USPAT;	2002/02/06 11:	10
_	131	esd adj protection.ti,ab. and bipolar adj transistor.ti,ab.	US-PGPUB;	2002/02/00 11:	77
		ctansistor.ci,ab.	EPO; JPO;		ļ
			DERWENT;		
			IBM TDB		
_	1	esd adj protection.ti,ab. and bipolar adj	USPAT;	2002/02/06 14:	06
		transistor.ti,ab. and plurality adj2	US-PGPUB;		
		(bipolar or transistor) and resist\$3 and	EPO; JPO;		
		parallel	DERWENT;		
	-		IBM_TDB		
-	12		USPAT;	2002/02/06 14:	08
		or purpose) near10 \$3bipolar adj	US-PGPUB;		İ
		transistor)	EPO; JPO; DERWENT;		
	ţ		IBM TDB		
	1	("0708550").PN.	USPAT;	2002/02/06 15:	07
_		(0700330).IN.	US-PGPUB;	2002/02/00 13.	,
			EPO; JPO;		
			DERWENT;		
			IBM_TDB		1
_	2	("5708550").PN.	USPAT;	2002/02/06 15:	35
 			US-PGPUB;		
			EPO; JPO;		
			DERWENT;		İ
	_	//#5042702#\ /#5700550#\ /#6060620#\	IBM_TDB USPAT	2002/02/06 15:	20
	7	((0010)02)	USPAT	2002/02/06 15:	20
		or ("5329143") or ("6172404") or ("5623387") or ("5272371")).PN.			
: : _	5		USPAT;	2002/02/06 15:	21
		("6268639") or ("5329143") or ("6172404")	US-PGPUB;		
		or ("5623387") or ("5272371")).PN.) and	EPO; JPO;		
		(base adj region and bipolar adj	DERWENT;		
		transistor)	IBM_TDB		}
_	0	(USPĀT;	2002/02/06 15:	35
		transistor.ti,ab. and path").PN.	US-PGPUB;		
ا			EPO; JPO;		
			DERWENT;		
ĺ		(11.23.24	IBM_TDB	2002/02/05 15	36
-	0	1 , 1	USPAT; US-PGPUB;	2002/02/06 15:	30
1		adj transistor.ti,ab. and path").PN.	EPO; JPO;		
,	1		DERWENT;		
			IBM TDB		
_	48	esd adj protection.ti,ab. and bipolar adj	USPAT;	2002/02/06 15:	38
		transistor.ti,ab. and path	US-PGPUB;		
			EPO; JPO;		
	1		DERWENT;		
			IBM TDB		

-	17	esd adj protection.ti,ab. and bipolar adj	USPAT;	2002/02/06 15:40
		transistor.ti,ab. and current adj path	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
	15	bipolar adj transistor and esd adj	USPAT;	2002/02/06 16:49
	13	protection and (increase near12 path)	US-PGPUB;	2002/02/00 10.49
		protection and (increase heariz path)	EPO; JPO;	
			DERWENT;	
			IBM TDB	,
_	12	bipolar adj transistor and esd adj	USPAT;	2002/02/06 17:01
		protection and ((base near10 (surround\$3	US-PGPUB;	
		or enclos\$3)) near10 (emitter or	EPO; JPO;	
		collector))	DERWENT;	
			IBM_TDB	
_	710	1 * *	USPAT;	2002/02/06 17:04
		near10 (surround\$3 or enclos\$3)) near10	US-PGPUB;	
		(emitter or collector))	EPO; JPO;	
			DERWENT;	
	506		IBM_TDB	0000/00/06 17-05
_	506	1 2	USPAT;	2002/02/06 17:05
		near5 (surround\$3 or enclos\$3)) near5	US-PGPUB;	
		(emitter or collector))	EPO; JPO; DERWENT;	
			IBM TDB	
_	334	bipolar adj transistor.ti,ab. and ((base	USPAT;	2002/02/06 17:05
_	334	near3 (surround\$3 or enclos\$3)) near3	US-PGPUB;	2002/02/00 17:03
]	(emitter or collector))	EPO; JPO;	
		(Chiletel of Collector)	DERWENT;	
			IBM TDB	
_	2	bipolar adj transistor.ti,ab. and ((base	USPAT;	2002/02/06 17:07
		near3 (surround\$3 or enclos\$3)) near3	US-PGPUB;	
		(emitter or collector)) and esd.ti,ab. and	EPO; JPO;	
		protection.ti,ab.	DERWENT;	
			IBM_TDB	
-	5	bipolar adj transistor.ti,ab. and ((base	USPĀT;	2002/02/06 17:10
		near4 (surround\$3 or enclos\$3)) near4	US-PGPUB;	
		(emitter or collector)) and (electrostatic	EPO; JPO;	
	,	adj discharge or esd).ti,ab. and	DERWENT;	
-	120	protection.ti,ab.	IBM_TDB USPAT;	2002/02/06 17:11
	430	bipolar adj transistor.ti,ab. and ((base near4 (surround\$3 or enclos\$3)) near4	US-PGPUB;	2002/02/08 17:11
		(emitter or collector))	EPO; JPO;	
		(emitter of coffector))	DERWENT;	*
			IBM TDB	
_	6	bipolar adj transistor.ti,ab. and ((base	USPAT;	2002/02/06 17:32
		near4 (surround\$3 or enclos\$3)) near4	US-PGPUB;	
		(emitter or collector)) and (esd with	EPO; JPO;	
		protection)	DERWENT;	
			IBM_TDB	
_	997	(257/355).CCLS.	USPAT;	2002/02/06 17:33
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	0.5	//NOCZ/OCCN/ GOTO / 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	IBM_TDB	2002/02/06 17 42
_	95	1 1 1	USPAT;	2002/02/06 17:42
		and bipolar adj transistor	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	4	((("257/355").CCLS.) and esd adj	USPAT;	2002/02/06 17:39
		protection and bipolar adj transistor) and	US-PGPUB;	-
		((base near7 (surround\$3 or enclos\$3))	EPO; JPO;	
		near7 (emitter or collector))	DERWENT;	
			IBM_TDB	
	1115	((257/360) or (257/361) or (257/362) or	USPAT;	2002/02/06 17:38
		(257/363)).CCLS.	US-PGPUB;	
	1		EPO; JPO;	
		I .		i '
			DERWENT; IBM TDB	

				<u>-</u>
_	122	((("257/360") or ("257/361") or	USPAT;	2002/02/06 17:39
		("257/362") or ("257/363")).CCLS.) and esd adj protection and bipolar adj transistor	US-PGPUB; EPO; JPO;	
		adj protection and bipotar adj cransistor	DERWENT;	
			IBM TDB	
_	6	(((("257/360") or ("257/361") or	USPĀT;	2002/02/06 17:42
		("257/362") or ("257/363")).CCLS.) and esd	US-PGPUB;	
		<pre>adj protection and bipolar adj transistor) and ((base near7 (surround\$3 or enclos\$3))</pre>	EPO; JPO; DERWENT;	
		near7 (emitter or collector))	IBM TDB	
_	893	((257/370) or (257/373)).CCLS.	USPAT;	2002/02/06 17:41
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	7	((("257/370") or ("257/373")).CCLS.) and	USPAT;	2002/02/06 17:42
	,	esd adj protection and bipolar adj	US-PGPUB;	2002, 02, 00 17:12
		transistor	EPO; JPO;	
			DERWENT;	
		(IBM_TDB	2002/02/06 10.25
_	0	(((("257/370") or ("257/373")).CCLS.) and esd adj protection and bipolar adj	USPAT; US-PGPUB;	2002/02/06 18:25
		transistor) and ((base near7 (surround\$3	EPO; JPO;	
[or enclos\$3)) near7 (emitter or	DERWENT;	
		collector))	IBM_TDB	
	192	bipolar adj transistor.ti,ab. and second	USPAT;	2002/02/06 18:28
		adj2 well	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	·
_	65		USPĀT;	2002/02/06 18:42
		well	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	2	lateral adj bipolar adj transistor.ti. and	USPAT;	2002/02/06 18:45
		second adj2 well	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	15	lateral adj bipolar adj transistor.ti,ab.	USPAT;	2002/02/06 18:45
		and second adj2 well	US-PGPUB;	·
	<u> </u>		EPO; JPO;	
			DERWENT; IBM TDB	
_	0	(source or drain) adj regions same	USPAT;	2002/02/07 08:33
	,	through-contact\$3	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	3	formed adj2 "same substrate" same	IBM_TDB USPAT;	2002/02/07 10:01
		plurality adj2 bipolar adj transistor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
· ·	4	(("5623387") or ("5043782") or ("6075271")	IBM_TDB USPAT	2002/02/07 10:02
-	4	(("5623387") or ("5043782") or ("6075271")	OSFAI	2002/02/0/ 10:02
_	0	jp-0361292351\$-\$.did.	USPAT;	2002/02/07 10:04
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	o	jp-361292351\$-\$.did.	USPAT;	2002/02/07 10:04
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	2	jp-61292351\$-\$.did.	USPAT;	2002/02/07 10:04
	[DE ATTACK TOWN	US-PGPUB;	_552,52,57 20.01
			EPO; JPO;	
			DERWENT;	•
	<u> </u>		IBM TDB	L

	<u></u>	(057/170)	TIODAM.	2002/11/05 19:14
-	3321	((257/168) or (257/173) or (257/355) or	USPAT;	2002/11/05 19:14
		(257/360) or $(257/361)$ or $(257/362)$ or $(257/362)$ or $(257/362)$	US-PGPUB;	
		(257/363) or (257/370) or (257/373)).CCLS.	EPO; JPO; DERWENT;	
			IBM TDB	
	110	(((257/168) or (257/173) or (257/355) or	USPAT;	2002/11/05 19:15
_	119	(((257/168) of (257/173) of (257/363) of (257/360) or (257/361) or (257/362) or	US-PGPUB;	2002/11/03 13:13
		(257/363) or (257/370) or	EPO; JPO;	
		(257/373)).CCLS.) and (uniformly or evenly	DERWENT;	
		or uniform or even) near12 (distribution	IBM TDB	
		or distributed)		
<u>_</u>	60	· ·	USPAT;	2002/11/05 19:19
_		(257/360) or (257/361) or (257/362) or	US-PGPUB;	
		(257/363) or (257/370) or	EPO; JPO;	
		(257/373)).CCLS.) and (uniformly or evenly	DERWENT;	
		or uniform or even) near12 (distribution	IBM TDB	
		or distributed) and (esd or electrostatic	_	
		adj discharge)		
_	44		USPAT;	2002/11/05 19:22
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	
		(257/363) or (257/370) or	EPO; JPO;	
		(257/373)).CCLS.) and (uniformly or evenly	DERWENT;	
		or uniform or even) near12 (distribution	IBM_TDB	
		or distributed) and (esd or electrostatic		
		adj discharge) and (resistor or		
		resistance) near15 (transistor or fet or		
		mis or mos or mosfet or misfet or igfet or	1	
		jfet or dmos or dmosfet or cmos or		
		cmosfet)		0000/06/00 00 00
-	45		USPAT;	2003/06/02 08:00
		US-5329143-\$ or US-5708550-\$ or	US-PGPUB;	
		US-4724471-\$ or US-5043782-\$ or	JPO;	
		US-5281841-\$ or US-5272371-\$ or	DERWENT	*
		US-5623387-\$ or US-5701024-\$ or		
		US-5689133-\$ or US-5637900-\$ or		
		US-6229182-\$ or US-5440162-\$ or US-5248892-\$ or US-6002156-\$ or	1	
		US-6277689-\$ or US-6002156-\$ or US-6277689-\$	1	
		US-6236086-\$ or US-5955763-\$ or		
		US-6172404-\$ or US-6268639-\$ or		
		US-5623156-\$ or US-6300649-\$ or		
		US-6306695-\$ or US-6388292-\$).did. or		
	1	(US-6441438-\$ or US-6441437-\$ or		
1		US-5763919-\$ or US-6388851-\$ or		
		US-4139935-\$ or US-4763184-\$ or		
		US-6097066-\$ or US-4806999-\$ or		
		US-5426323-\$ or US-6445039-\$ or		
		US-4736271-\$ or US-5237395-\$ or		
	0)(0	US-5939756-\$ or US-5982600-\$ or		
		US-6078068-\$).did. or (US-20020003236-\$ or		
		US-20020014665-\$).did. or		
		(JP-61292351-\$).did. or		
		(JP-61292351-\$).did.		

				1 2 2 2 4 2 2 4 2 2 4 2 4 2
-	1	((US-5565698-\$ or US-5742083-\$ or	USPAT;	2003/06/02 08:10
		US-5329143-\$ or US-5708550-\$ or	US-PGPUB;	
		US-4724471-\$ or US-5043782-\$ or	JPO;	
		US-5281841-\$ or US-5272371-\$ or	DERWENT	
		US-5623387-\$ or US-5701024-\$ or		
		US-5689133-\$ or US-5637900-\$ or		
		US-6229182-\$ or US-5440162-\$ or		
		US-5248892-\$ or US-6002156-\$ or		
		US-6277689-\$ or US-6075271-\$ or		
		US-6236086-\$ or US-5955763-\$ or		:
		US-6172404-\$ or US-6268639-\$ or		
		· ·		
		US-5623156-\$ or US-6300649-\$ or		
		US-6306695-\$ or US-6388292-\$).did. or		
		(US-6441438-\$ or US-6441437-\$ or		
		US-5763919-\$ or US-6388851-\$ or		
		US-4139935-\$ or US-4763184-\$ or		:
		US-6097066-\$ or US-4806999-\$ or		
		US-5426323-\$ or US-6445039-\$ or		
		US-4736271-\$ or US-5237395-\$ or		
		US-5939756-\$ or US-5982600-\$ or		
		US-6078068-\$).did. or (US-20020003236-\$ or		
		US-20020014665-\$).did. or		
		(JP-61292351-\$).did. or		
		(JP-61292351-\$).did.) and wada.in.		0000/05/00 00 00
-	2	((US-5565698-\$ or US-5742083-\$ or	USPAT;	2003/06/02 08:29
		US-5329143-\$ or US-5708550-\$ or	US-PGPUB;	
		US-4724471-\$ or US-5043782-\$ or	JPO;	
		US-5281841-\$ or US-5272371-\$ or	DERWENT	:
		US-5623387-\$ or US-5701024-\$ or		
		US-5689133-\$ or US-5637900-\$ or		
		US-6229182-\$ or US-5440162-\$ or		
		US-5248892-\$ or US-6002156-\$ or		1
		US-6277689-\$ or US-6075271-\$ or		
		US-6236086-\$ or US-5955763-\$ or		
		US-6172404-\$ or US-6268639-\$ or		
		US-5623156-\$ or US-6300649-\$ or		*
		US-6306695-\$ or US-6388292-\$).did. or		,
		(US-6441438-\$ or US-6441437-\$ or		
		US-5763919-\$ or US-6388851-\$ or		
		US-4139935-\$ or US-4763184-\$ or		·
		US-6097066-\$ or US-4806999-\$ or		
		US-5426323-\$ or US-6445039-\$ or		·
		US-4736271-\$ or US-5237395-\$ or		·
		US-5939756-\$ or US-5982600-\$ or		
		US-6078068-\$).did. or (US-20020003236-\$ or		
		US-20020014665-\$).did. or		
		(JP-61292351-\$).did. or	,	
		(JP-61292351-\$).did.) and avery.in.		
_	0		USPAT;	2003/06/02 08:30
		•	US-PGPUB;	
			JPO;	
			DERWENT	
		transistan add armay and control accus		2003/06/02 08:33
_	9	, ,	USPAT;	2003/00/02 08:33
		(connexion connection)	US-PGPUB;	1
			JPO;	
		\$	DERWENT	1
-	7	transistor adj array and shunt adj	USPAT;	2003/06/02 08:36
		resistor.	US-PGPUB;	1
			JPO;	
			DERWENT	
_	1	shunt adj resistor near4 (separate each	USPAT;	2003/06/02 08:38
	1	every) and (257/\$6.ccls. 438/\$6.ccls.)	US-PGPUB;	2000,00,02 00.50
	:	every, and (257/90.0018. 450/90.0018.)		
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	21	shunt adj resistor near4 (separate each	USPAT;	2003/06/02 08:40
		every)	US-PGPUB;	
			EPO; JPO;	[
			DERWENT;	
			IBM TDB	į l
I .	I	I	, <u></u>	F

-	0	shunt adj resistor near4 (separate each	USPAT;	2003/06/02 08:41
		every) and transistor and array	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	266	resistor near4 (separate each every) and	USPAT;	2003/06/02 08:52
		transistor and array	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	7	(bipolar adj transistor igbt) near2 array	USPAT;	2003/06/02 08:58
		and base near3 resistor	US-PGPUB;	
			EPO; JPO;	
į	,		DERWENT;	
			IBM TDB	
_	16	shunt adj resistance and bipolar adj	USPAT;	2003/06/02 09:06
-	10	transistor and array	US-PGPUB;	2003,00,02 03.00
	*	transistor and array	EPO; JPO;	
1				
			DERWENT;	
		(4057/160) (057/170) (057/175)	IBM_TDB	2002/06/02 00 07
_	3290	((257/168) or (257/173) or (257/355) or	USPAT;	2003/06/02 09:07
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	
]	(257/370) or (257/373)).CCLS.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12		USPAT;	2003/06/02 09:09
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	
		(257/370) or (257/373)).CCLS.) and bipolar	EPO; JPO;	
		adj transistor near5 array and resistor	DERWENT;	
			IBM TDB	
_	6	bipolar adj transistor near5 array and	USPAT;	2003/06/02 09:16
		resistor and (esd electrostatic adj	US-PGPUB;	
		discharge)	EPO; JPO;	
		, , . , . ,	DERWENT;	
			IBM TDB	
l <u> </u>	2	("6472286").PN.	USPAT;	2003/06/02 12:11
	-	(01/2200) . 211.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	"6008524".PN.	USPAT	2003/06/02 09:17
_	1	"5850095".PN.	USPAT	2003/06/02 09:17
-	3484		USPAT;	2003/06/07 03:23
-	3404		US-PGPUB;	2003/00/07 17.38
		(257/360) or (257/361) or (257/362) or		
		(257/362) or (257/363) or (257/370) or	EPO; JPO;	
		(257/373)).CCLS.	DERWENT;	
		(4,4057,4160) (057,4170) (057,4057)	IBM_TDB	0000/06/07 17 10
_	641		USPAT;	2003/06/07 17:40
		(257/360) or (257/361) or (257/362) or	US-PGPUB;	
		(257/362) or (257/363) or (257/370) or	EPO; JPO;	
8		(257/373)).CCLS.) and (electrostatic adj	DERWENT;	
		discharge esd).ti,ab,clm.	IBM_TDB	
-	17		USPAT;	2003/06/07 17:45
[(257/360) or (257/361) or (257/362) or	US-PGPUB;	
		(257/362) or (257/363) or (257/370) or	EPO; JPO;	
		(257/373)).CCLS.) and (electrostatic adj	DERWENT;	
		discharge esd).ti,ab,clm. and protect\$3	IBM_TDB	
		near12 parallel near12 (resistor	_	
		resistance)		
_	0		USPAT;	2003/06/07 17:46
		esd).ti,ab,clm. and protect\$3 near12	US-PGPUB;	
		parallel near12 track near2 (resistor	EPO; JPO;	
1		resistance)	DERWENT;	
			IBM TDB	
_	76	(electrostatic adj discharge	USPAT;	2003/06/07 17:48
	[,5]	esd).ti,ab,clm. and protect\$3 near12	US-PGPUB;	
		parallel near12 (resistor resistance)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
I .	I		TDG IND	<u> </u>

	I 50	(electrostatic adj discharge	USPAT;	2003/06/07 18:42
_	58	esd).ti,ab,clm. and protect\$3 near12	US-PGPUB;	2003/08/07 10:42
	•	parallel near12 (resistor resistance) and	EPO; JPO;	
			l .	
		transistor	DERWENT;	
		(HE040700H) TV	IBM_TDB	2002/06/07 19:01
-	2	("5043782").PN.	USPAT;	2003/06/07 19:01
			US-PGPUB;	
	_		EPO; JPO;	•
			DERWENT;	
			IBM_TDB	
-	2	("6075271").PN.	USPAT;	2003/06/07 19:02
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	118		USPAT;	2003/06/11 15:32
		switching adj2 device.ti,ab,clm.	US-PGPUB;	·
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
l –	182	schottky adj (contact barrier) and	USPĀT;	2003/06/11 15:33
		switching near3 device.ti,ab,clm.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
*			IBM TDB	
_	235	schottky adj (contact barrier) and (switch	USPAT;	2003/06/11 15:34
1		switching) near3 device.ti,ab,clm.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	8	(("5345357") or ("5898206") or ("5910677")	USPĀT;	2004/04/10 18:37
		or ("6469354")).PN.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	•
			IBM TDB	~
_	2	("5043782").PN.	USPAT;	2004/04/10 18:40
		1 3033702 7.24.	US-PGPUB;	2001,01,10 10.40
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
l _	0	("jp-61292351\$-\$.did.").PN.	USPAT;	2004/04/10 18:40
		/ Jp organity youru. J. EN.	US-PGPUB;	2004/04/10 10.40
			EPO; JPO;	
			DERWENT;	
		, and the second	IBM TDB	
	2	in 612022516 6 did	USPAT;	2004/04/10 18:52
_	1	jp-61292351\$-\$.did.		2004/04/10 10:32
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	1